Supplementary Information

Tunable Broadband Near-Infrared Luminescence from Cr³⁺-Doped Gallium Oxide-Based Phosphors for Advanced Sensing and LED Applications

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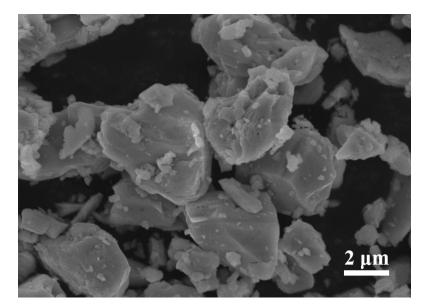


Figure S1. The SEM image of Ga_{1.57}Zn_{0.2}Ge_{0.2}Cr_{0.03}O₃ phosphor.

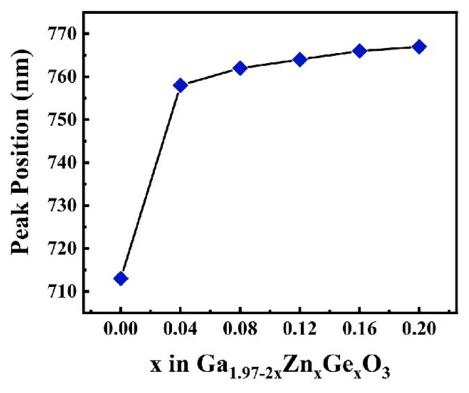


Figure S2. The emission spectra of peak position as a function of x in $Ga_{1.97-2x}Zn_xGe_xCr_{0.03}O_3$ (x = 0 - 0.2) phosphors.

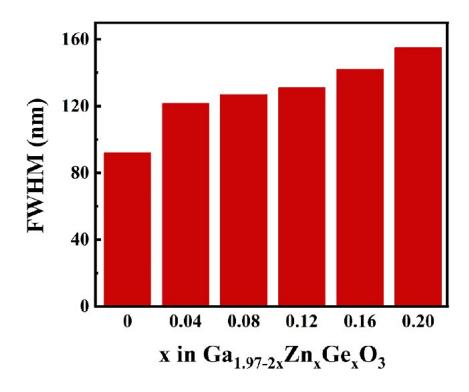


Figure S3. The emission spectra of FWHM as a function of x in $Ga_{1.97-2x}Zn_xGe_xCr_{0.03}O_3$ (x = 0-0.2) phosphors.

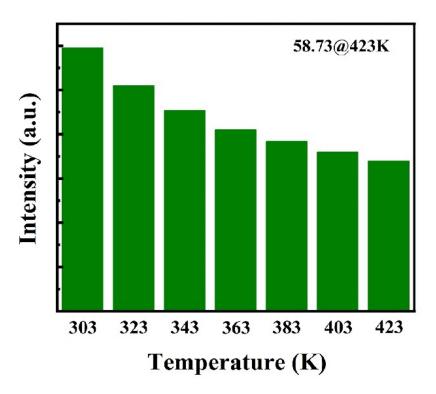


Figure S4. The intensity histograms of $Ga_{1.57}Zn_{0.2}Ge_{0.2}Cr_{0.03}O_3$ at temperature ranges of 303 K-423 K.

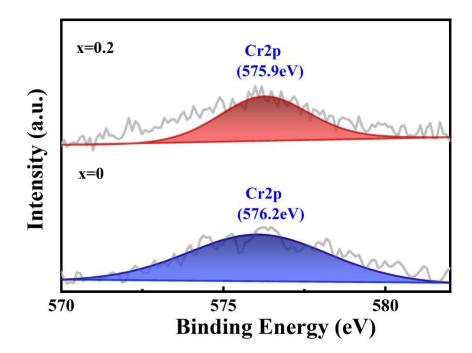


Figure S5. High-resolution Cr 2p XPS core energy level spectrum of $Ga_{2-2x}Zn_xGe_xCr_{0.03}O_3$ doped with different co-unit concentrations.

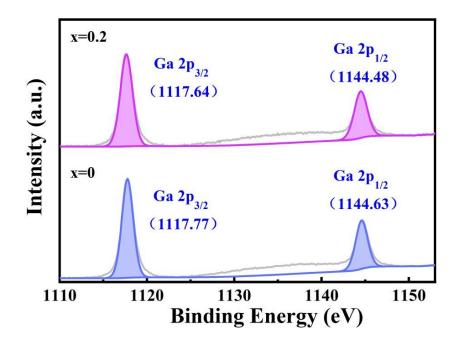


Figure S6. High-resolution Ga 2p XPS core energy level spectrum of $Ga_{2-2x}Zn_xGe_xCr_{0.03}O_3doped$ with different co-unit concentrations.